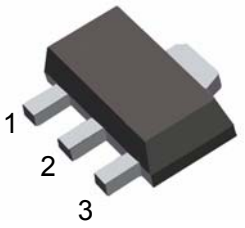
TRANSISTOR (NPN)

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

- Low $V_{CE(sat)}$.$V_{CE(sat)}$ = 0.2V (Typ.)(I_C / I_B = 2A / 0.1A)
- Excellent current gain characteristics.
- Complements to 2SA1585

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	20	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	3	A
P_C	Collector Power Dissipation	500	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 50μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA , I_B=0	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=50μA, I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=30V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=2V, I_C= 0.1A	120		560	
Collector-emitter saturation voltage*	V_{CEsat}	I_C= 2A, I_B=0.1A			0.5	V
Transition frequency	f_T	V_{CE}=2V, I_C=0.5 A F=100MHz	200	290		MHz

***pulse test**

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560
marking	4115Q	4115R	4115S

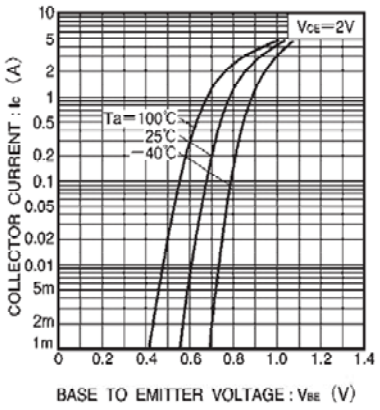


Fig.1 Grounded emitter propagation characteristics

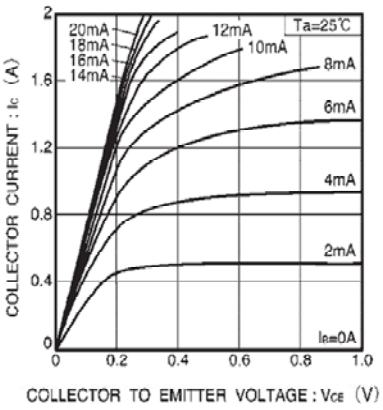


Fig.2 Grounded emitter output characteristics (Ⅰ)

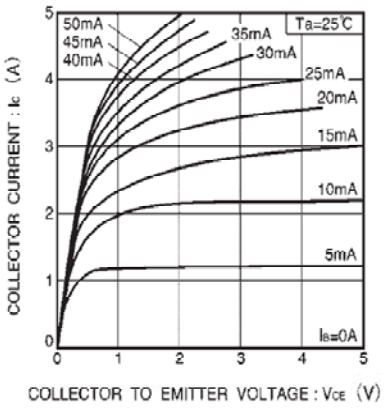


Fig.3 Grounded emitter output characteristics (Ⅱ)

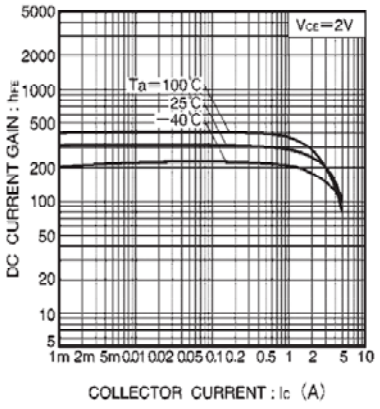


Fig.4 DC current gain vs. collector current

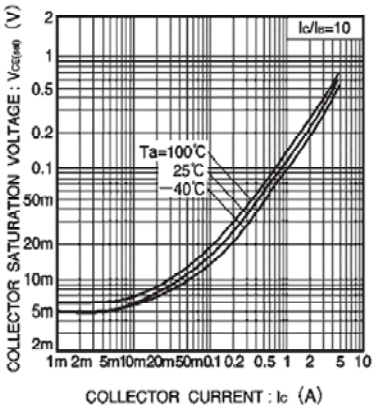


Fig.5 Collector-emitter saturation voltage vs. collector current (Ⅰ)

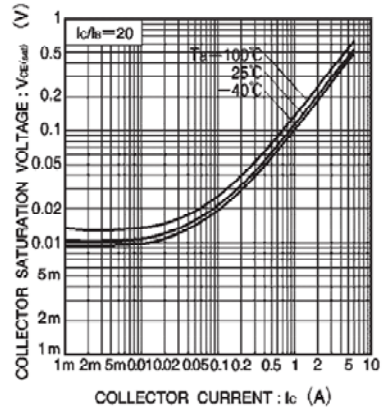


Fig.6 Collector-emitter saturation voltage vs. collector current (Ⅱ)

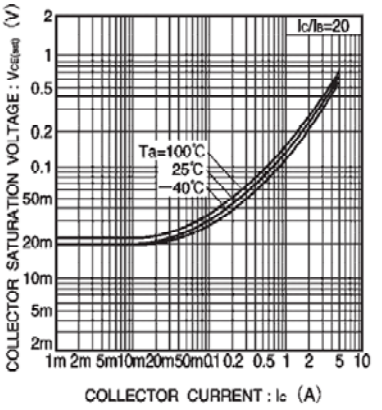


Fig.7 Collector-emitter saturation voltage vs. collector current (Ⅲ)

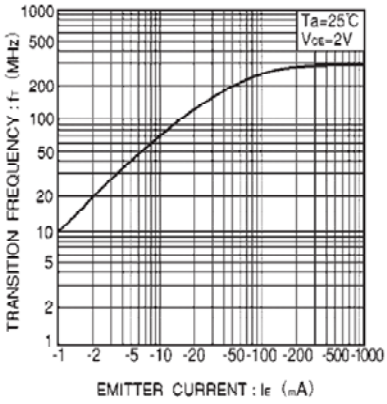


Fig.8 Gain bandwidth product vs. emitter current

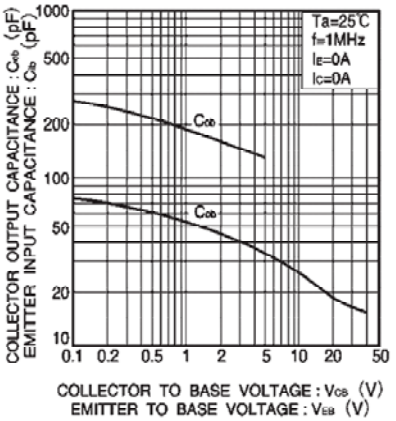


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage